

Spezifikationen	
Artikelnummer	MJD117TF
Hersteller	Fairchild/ON Semiconductor
Beschreibung	TRANS PNP DARL 100V 2A DPAK
Kategorie	Diskrete Halbleiterprodukte > Transistoren-Bipolar
Teilstatus	1286 pcs Stock
Spannung - Kollektor-Emitter-Durchbruch (max)	100V
VCE Sättigung (Max) @ Ib, Ic	3V @ 40mA, 4A
Transistor-Typ	PNP - Darlington
Supplier Device-Gehäuse	D-Pak
Serie	-
Leistung - max	1.75W
Verpackung	Tape & Reel (TR)
Verpackung / Gehäuse	TO-252-3, DPak (2 Leads + Tab), SC-63
Betriebstemperatur	150°C (TJ)
Befestigungsart	Surface Mount
Frequenz - Übergang	25MHz
DC Stromgewinn (HFE) (Min) @ Ic, VCE	1000 @ 2A, 3V
Strom - Collector Cutoff (Max)	20µA
Strom - Kollektor (Ic) (max)	2A

sein:

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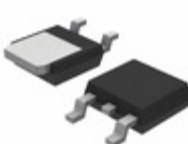
MJD117T4G MOS
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MJD122-1
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TRANS NPN DARL 100V 8A
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Mehr

Schlüsselwort: Semiconductor MJD117TF Datenblatt	MJD117TF-Datenblätter	MJD117TF PDF	Fairchild/ON Semiconductor MJD117TF
MJD117TF Electronic	MJD117TF-Komponenten	MJD117TF-Verteiler	MJD117TF-Bild
MJD117TF Preis	MJD117TF Hersteller	MJD117TF Bild	MJD117TF Aktie
MJD117TF Neu	MJD117TF Original	MJD117TF garantiert	MJD117TF RFQ
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